

FIG. 1

FIG. 2-(1)

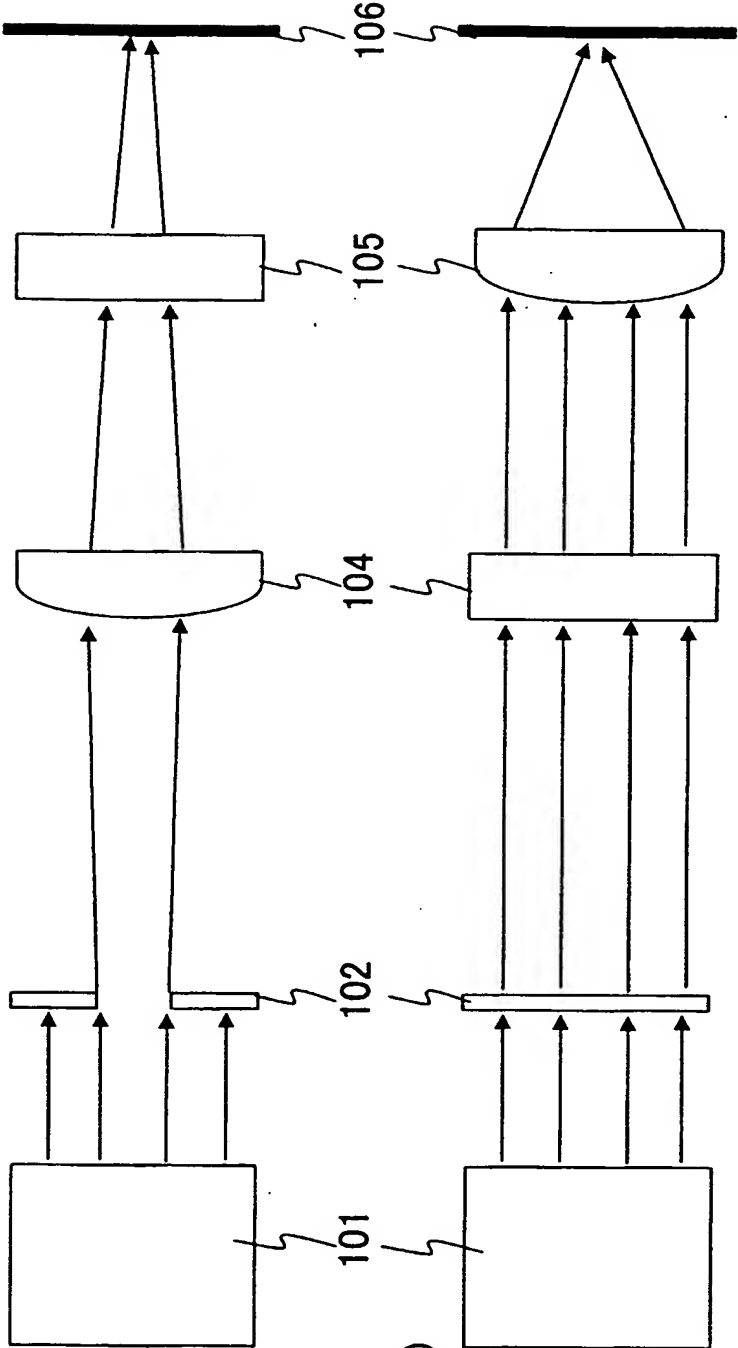
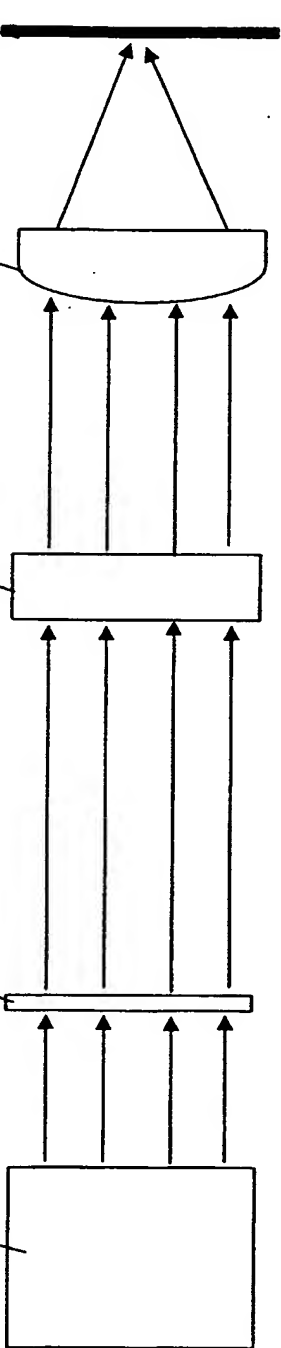


FIG. 2-(2)



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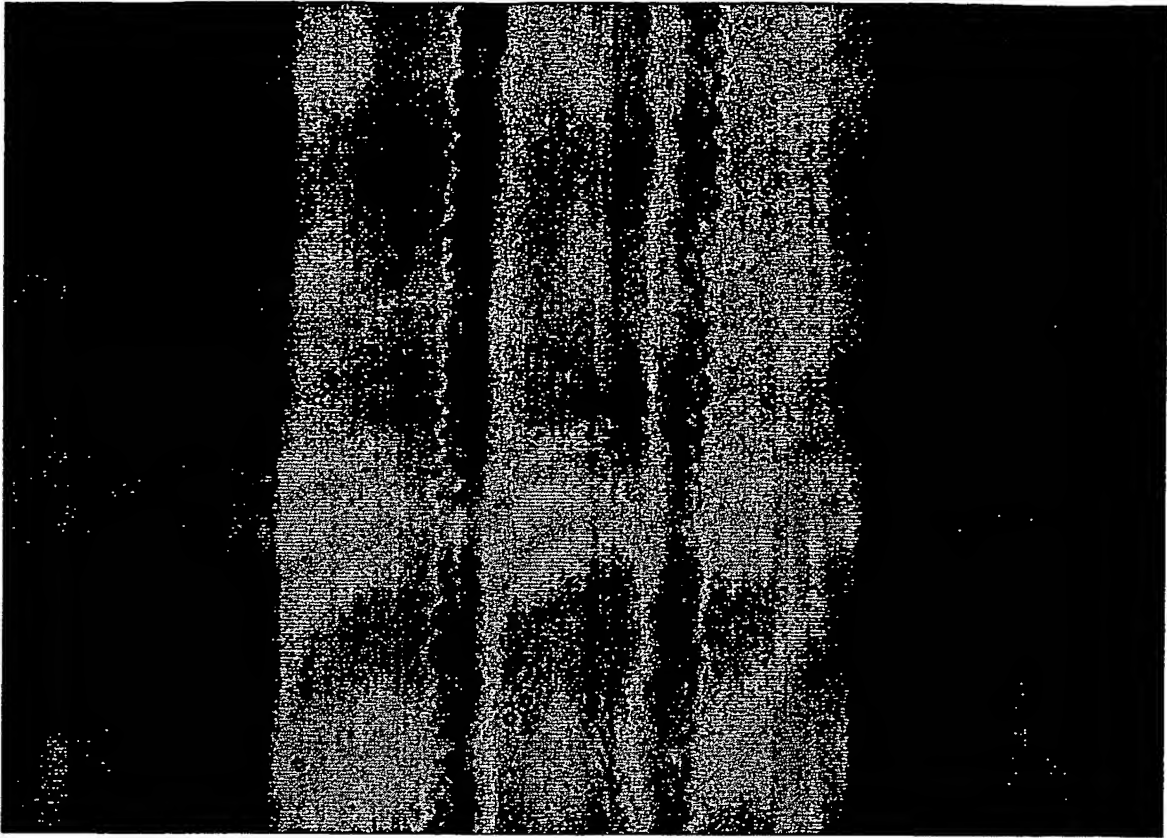


FIG. 3

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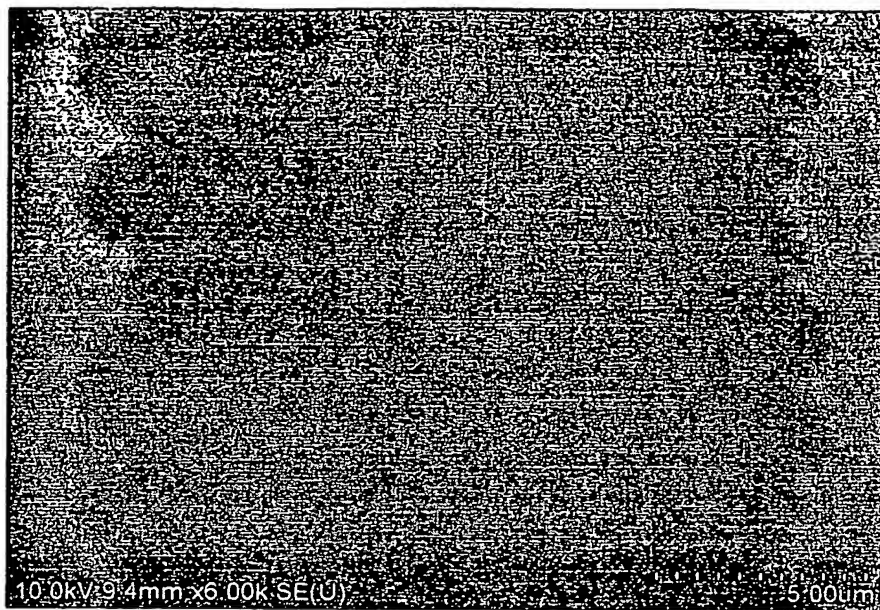


FIG. 4

FIG. 5A

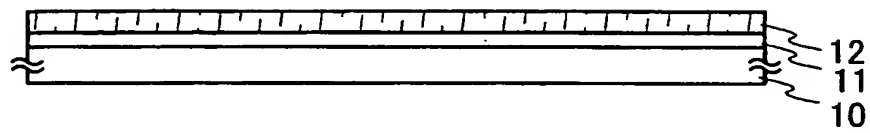


FIG. 5B

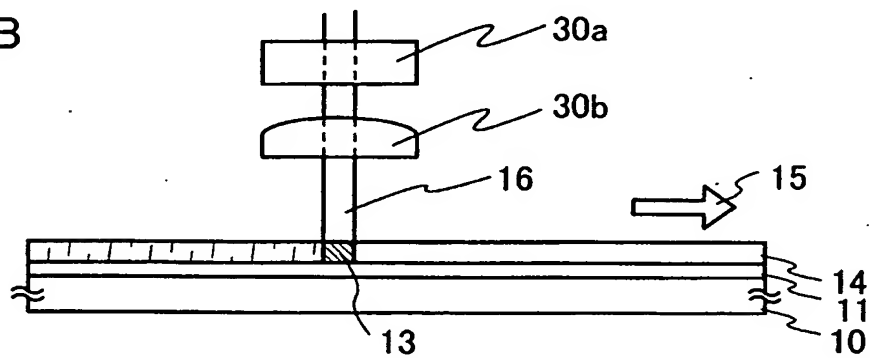


FIG. 5C

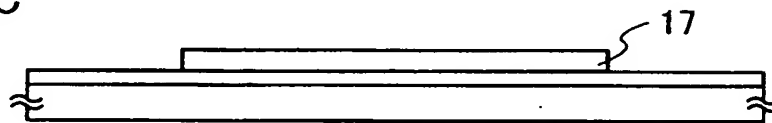


FIG. 5D

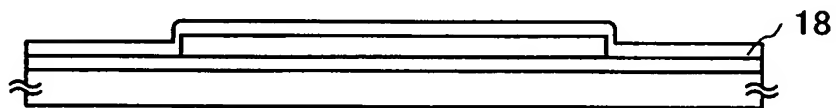
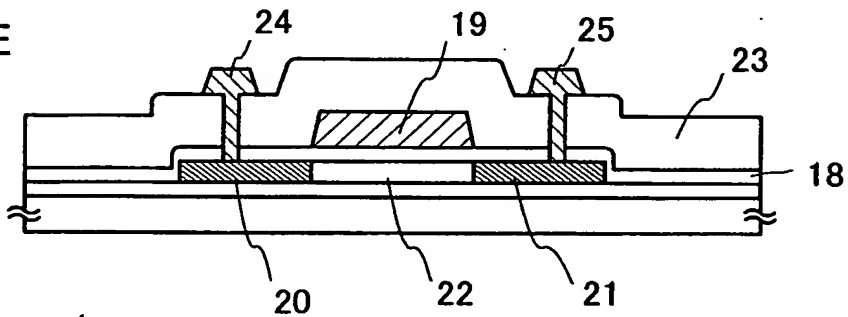


FIG. 5E



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FIG. 6A

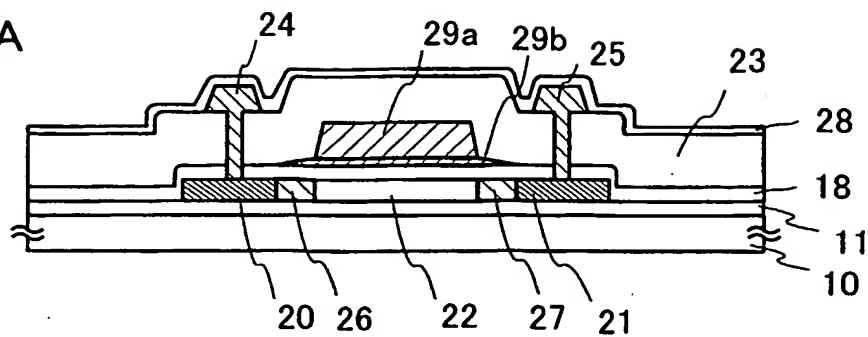
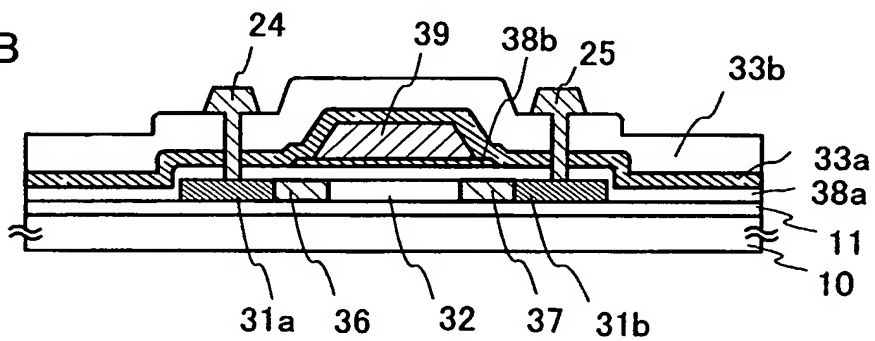


FIG. 6B



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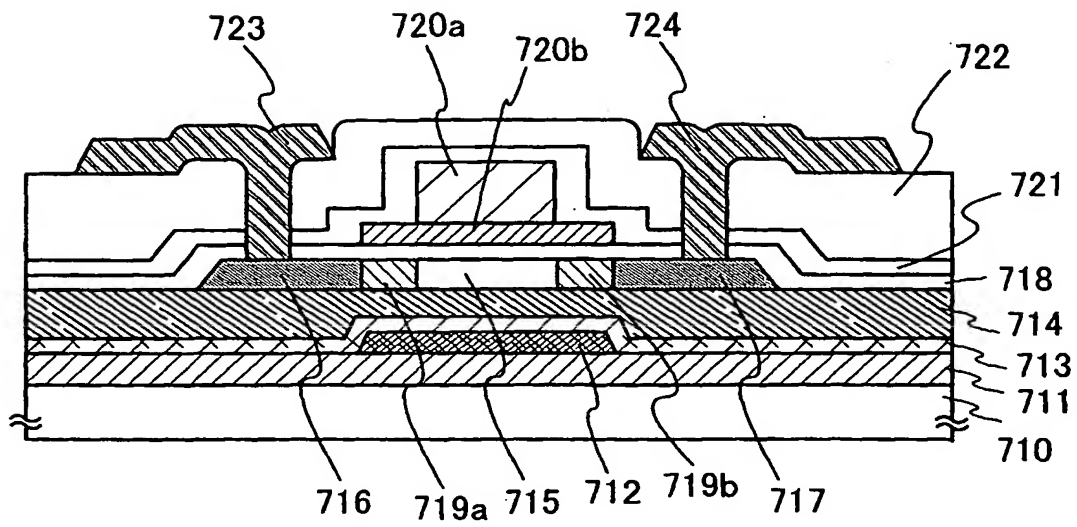


FIG. 7

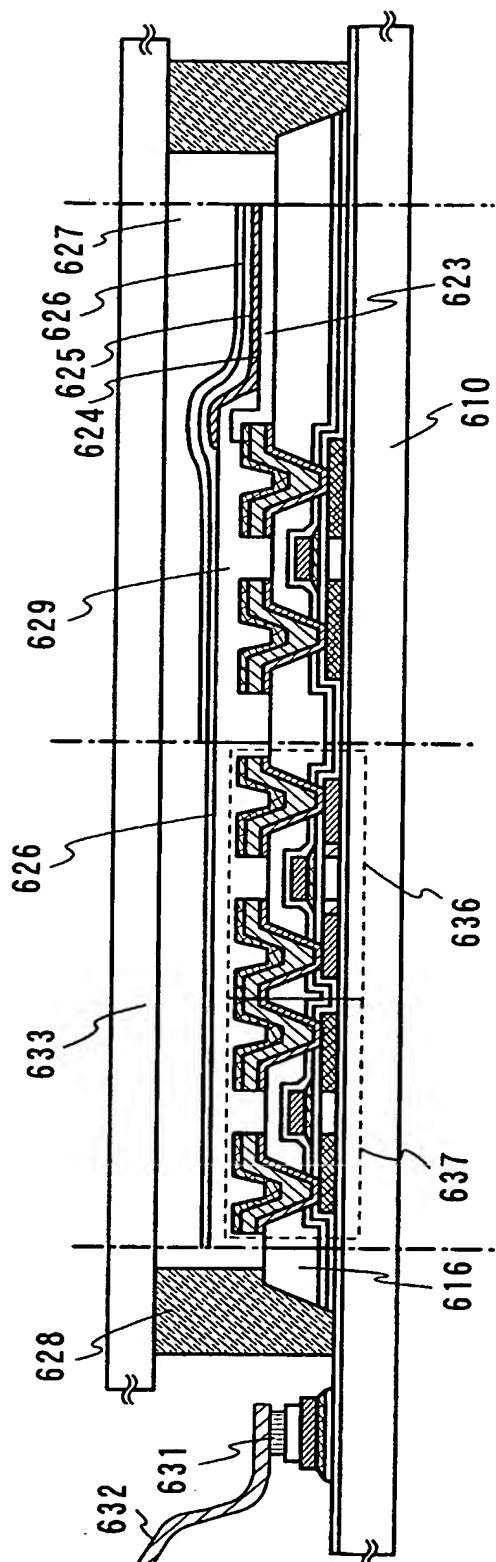


FIG. 8

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FIG. 9A

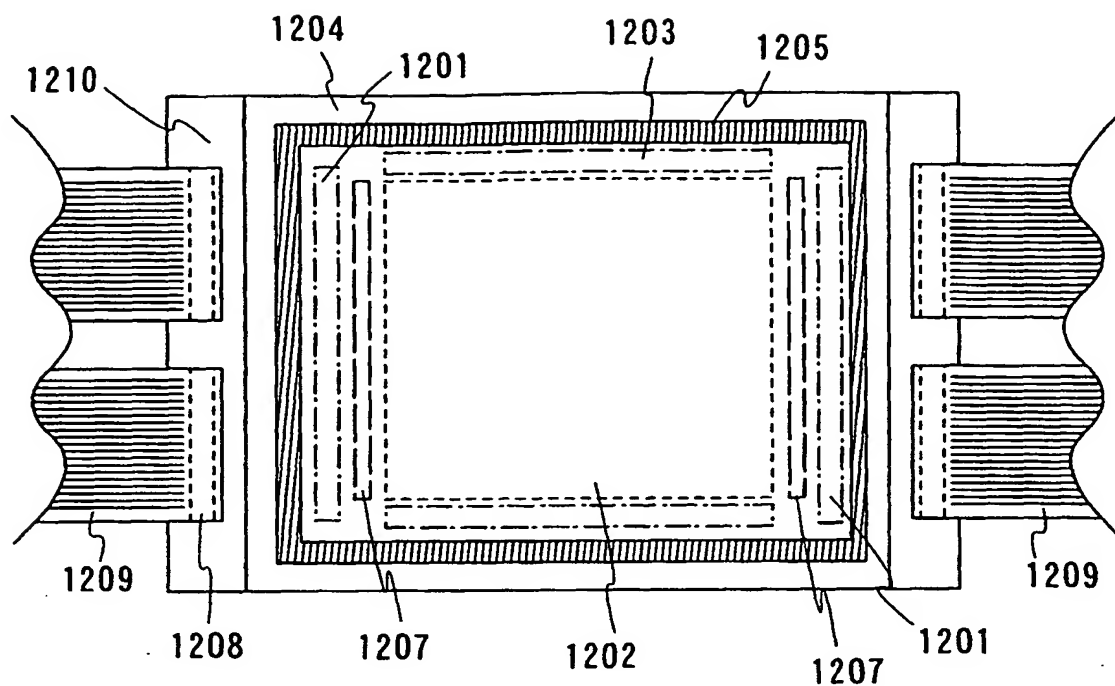
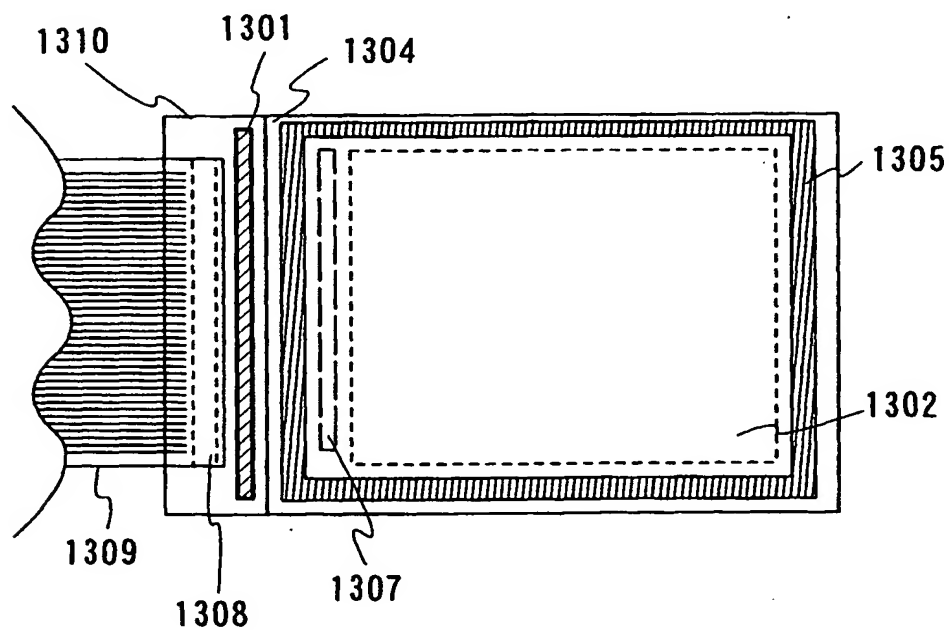


FIG. 9B



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FIG. 10A

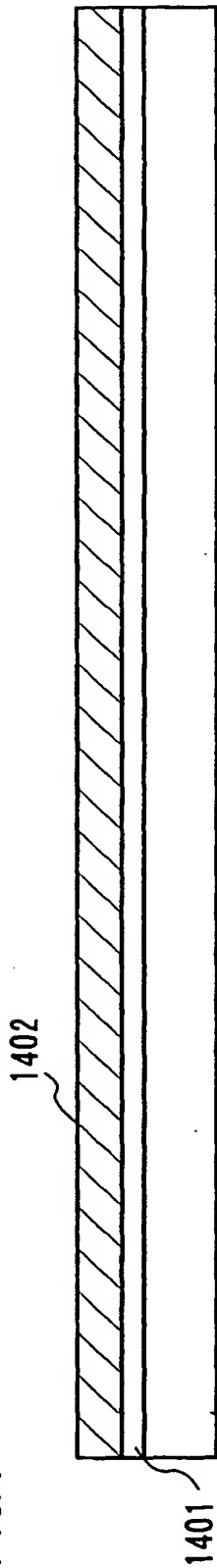


FIG. 10B

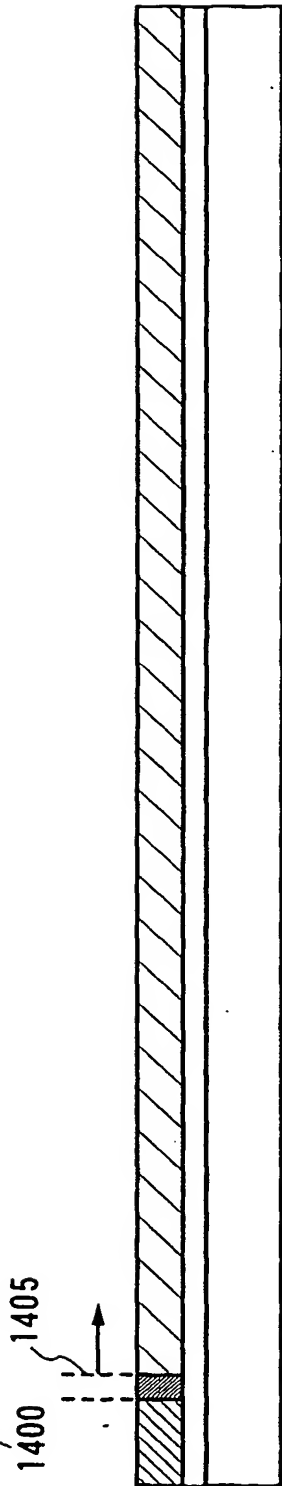
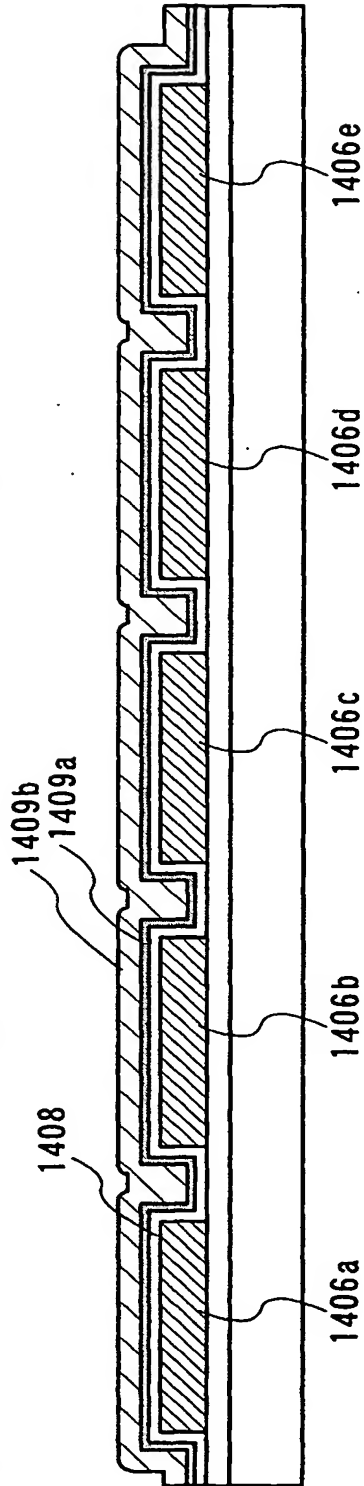


FIG. 10C



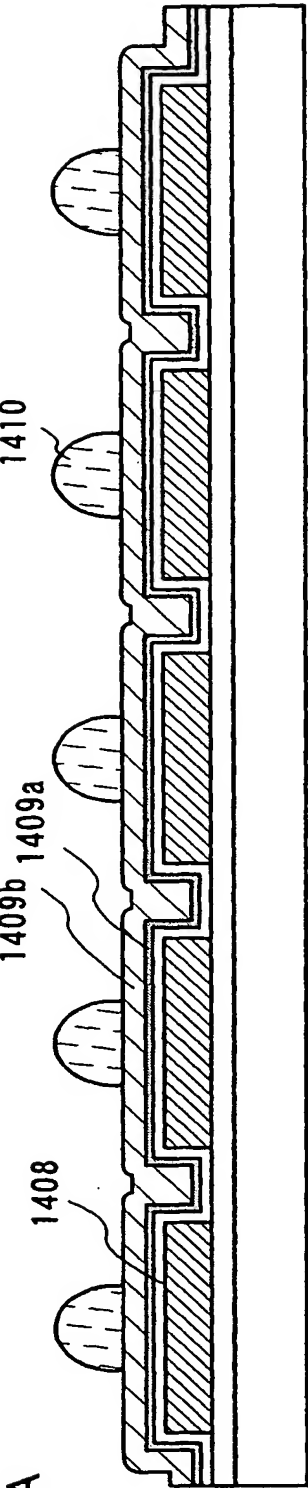


FIG. 11A

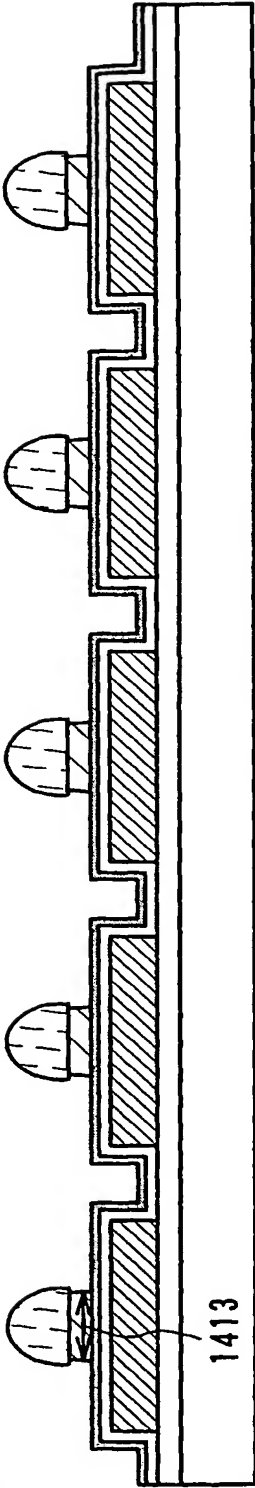


FIG. 11B

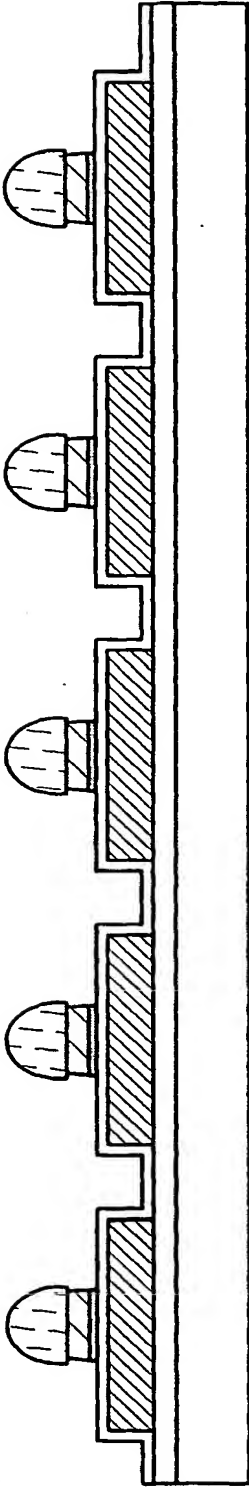


FIG. 11C

FIG. 12A

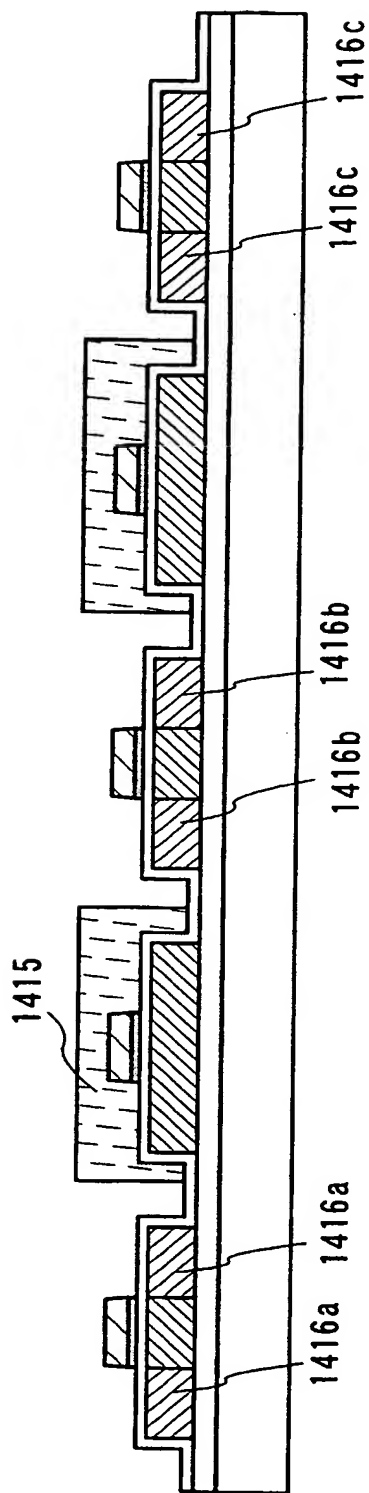


FIG. 12B

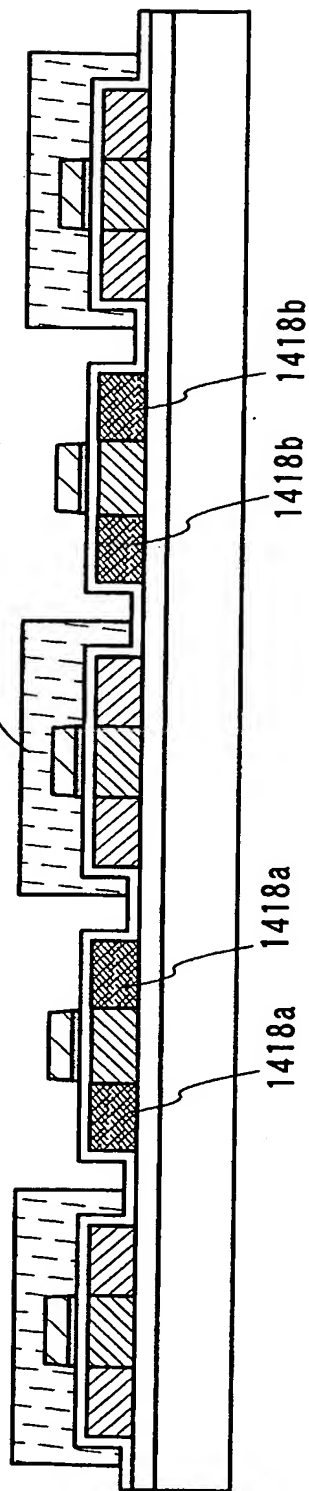


FIG. 12C

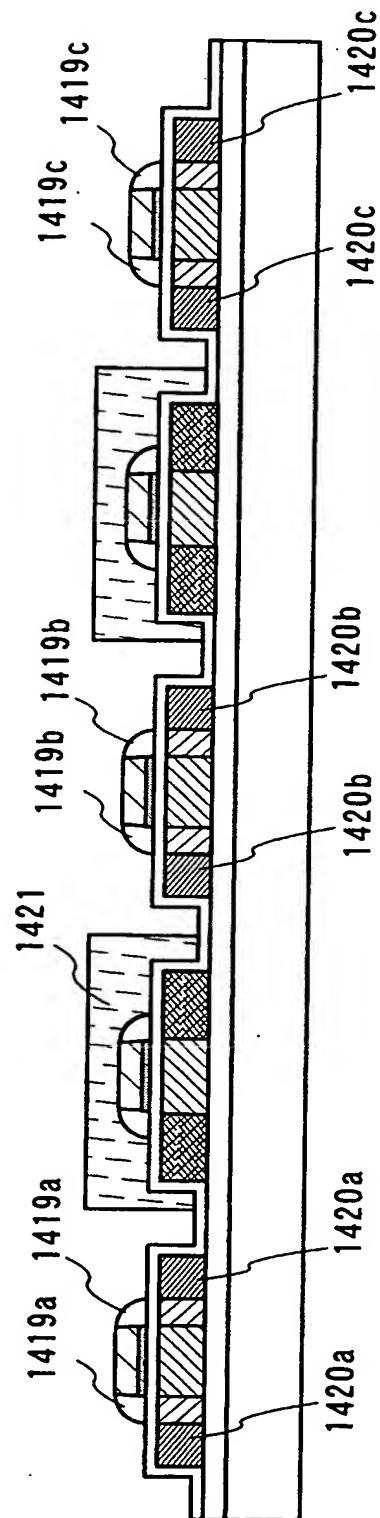


FIG. 13A

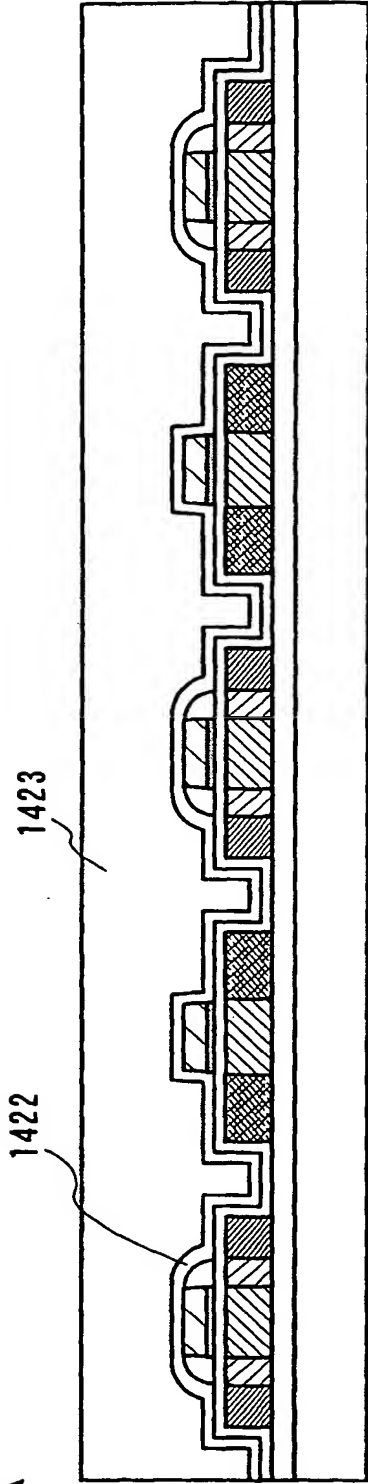
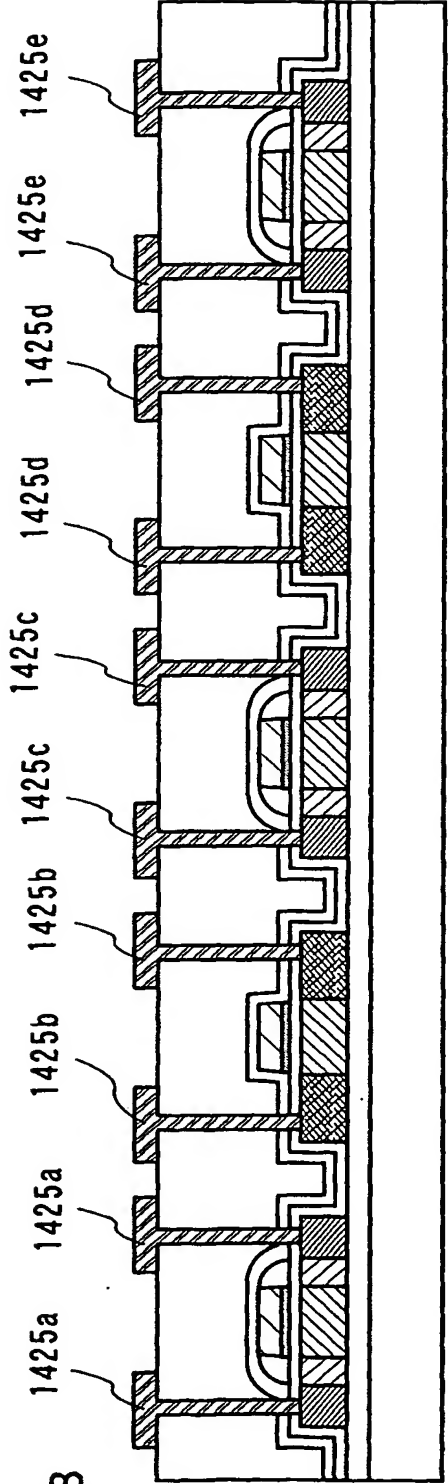


FIG. 13B



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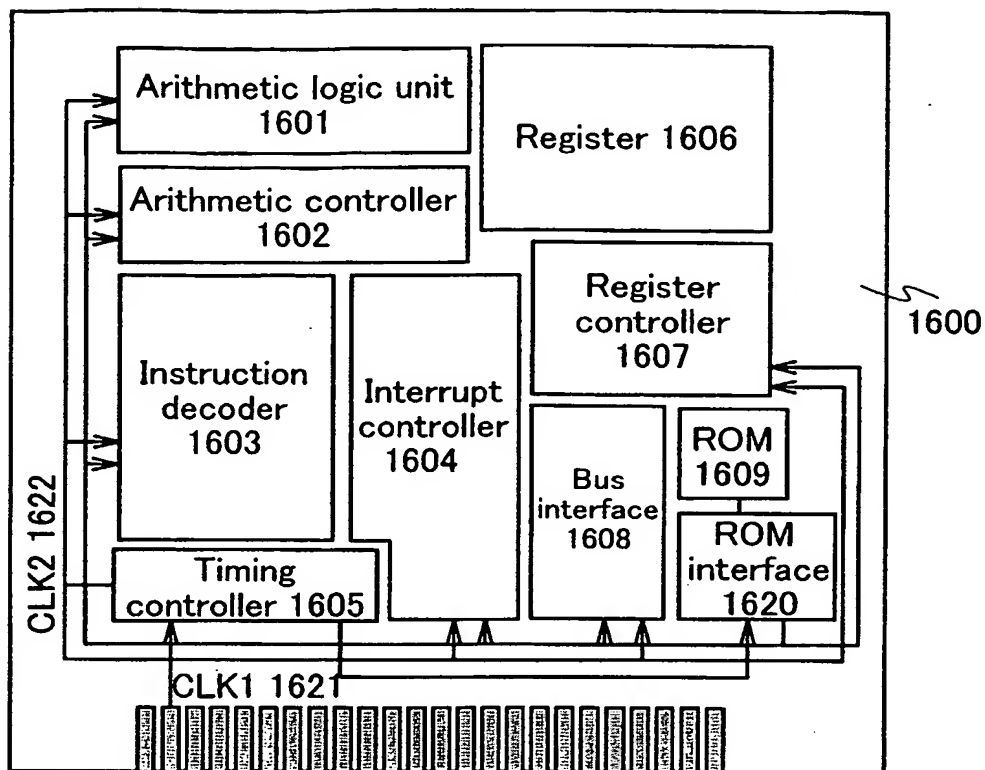


FIG. 14

FIG. 15A

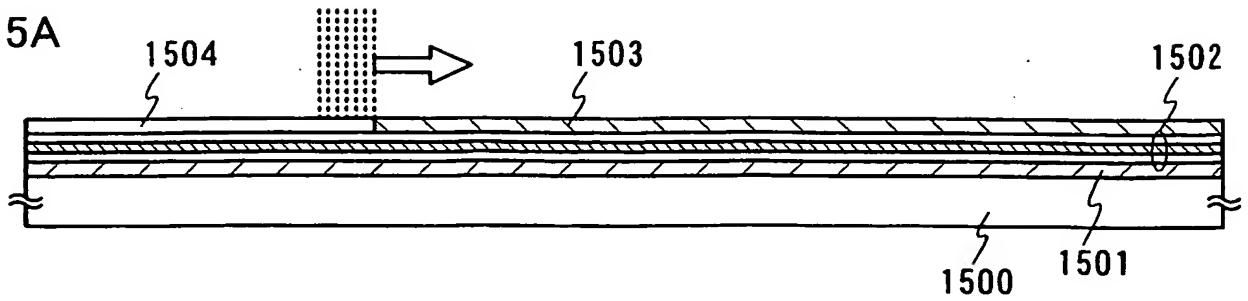


FIG. 15B

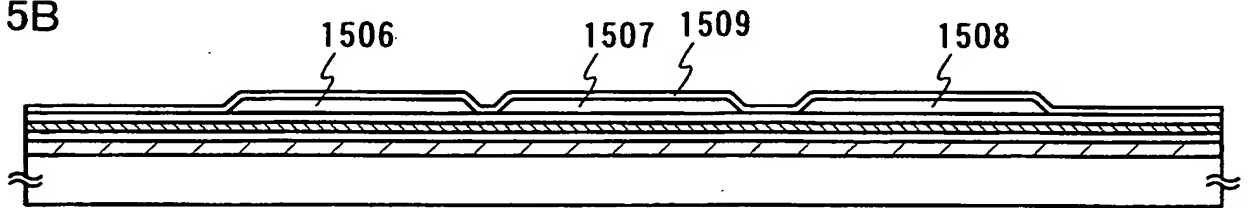


FIG. 15C

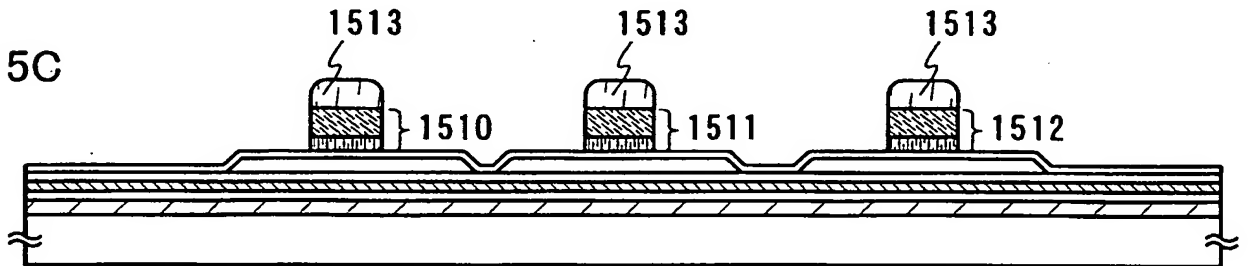


FIG. 15D

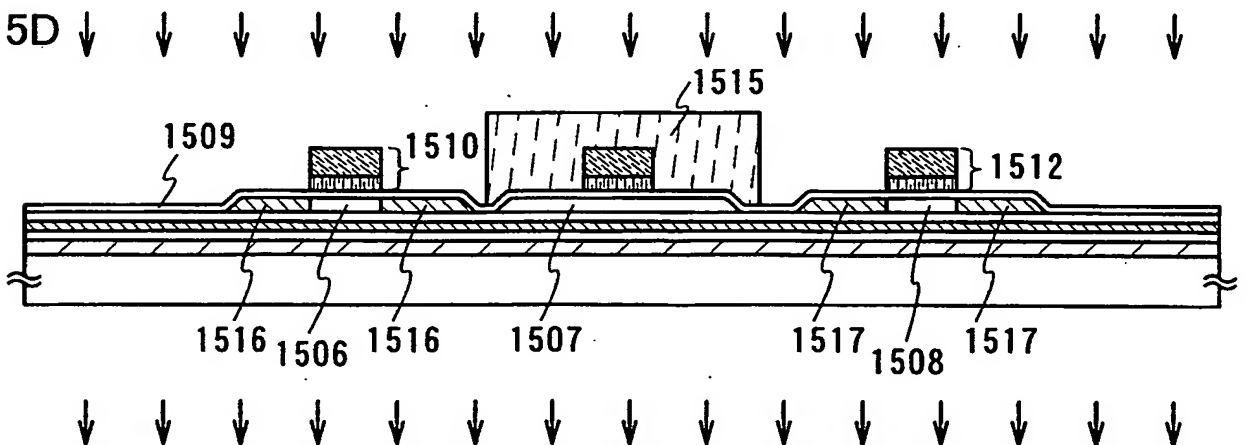
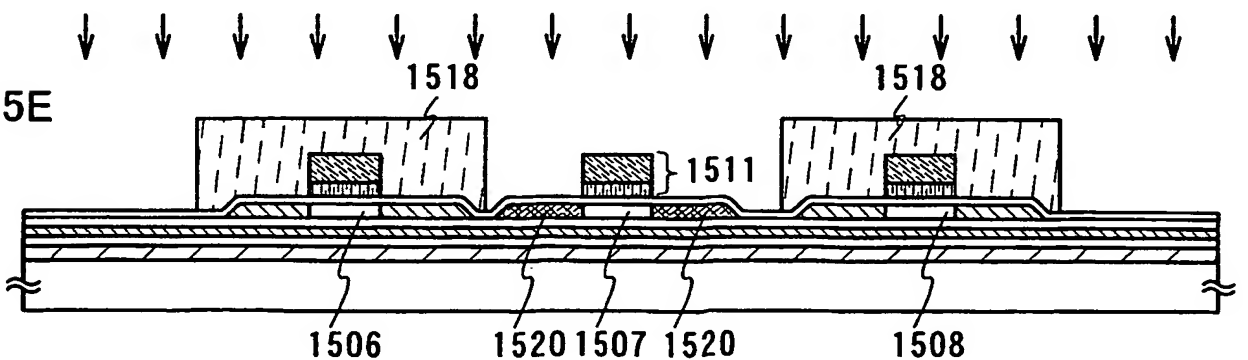


FIG. 15E



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FIG. 16A

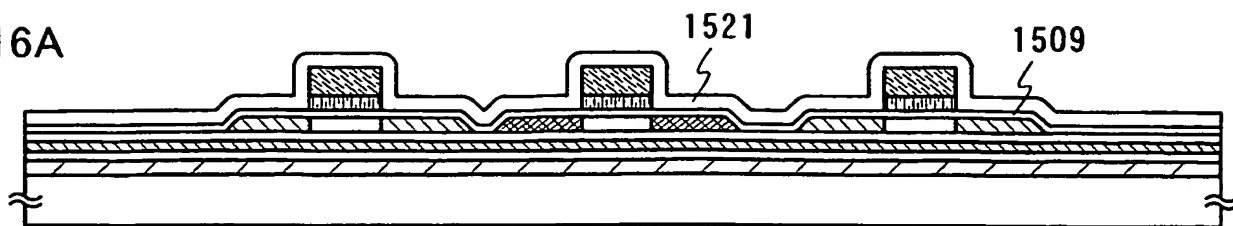


FIG. 16B

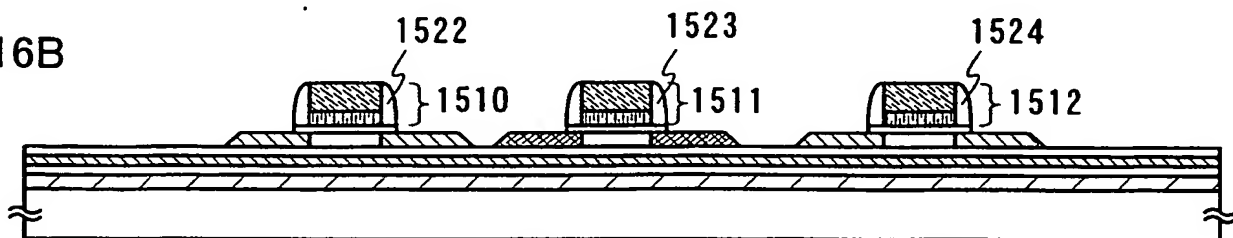


FIG. 16C

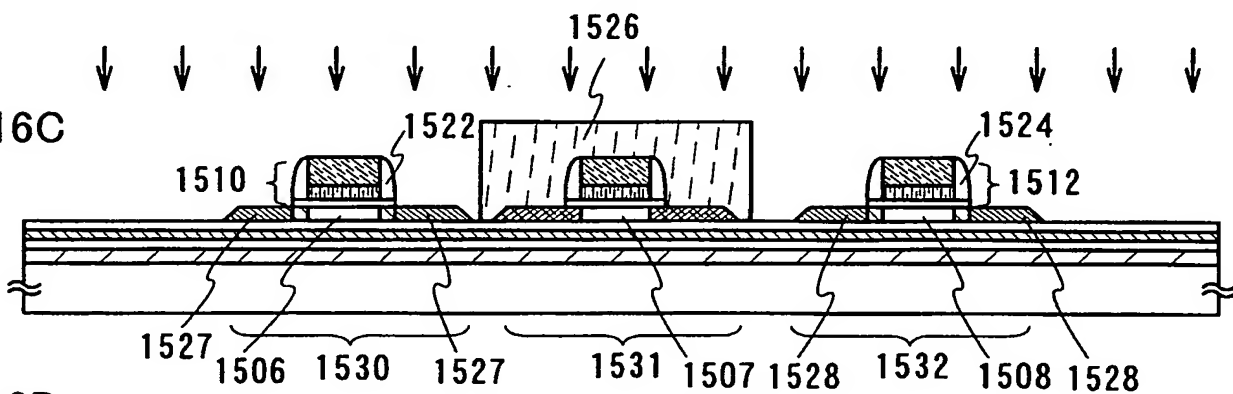


FIG. 16D

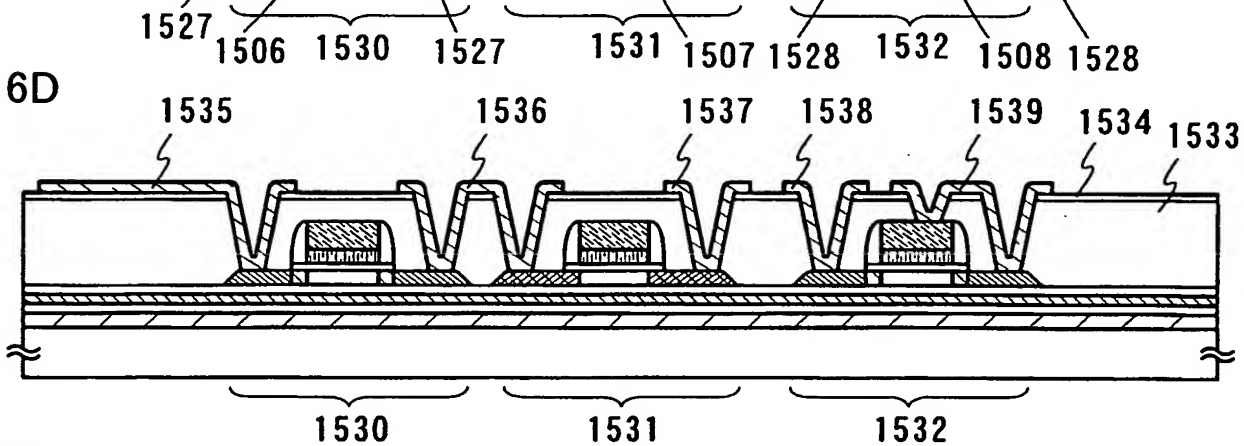


FIG. 16E

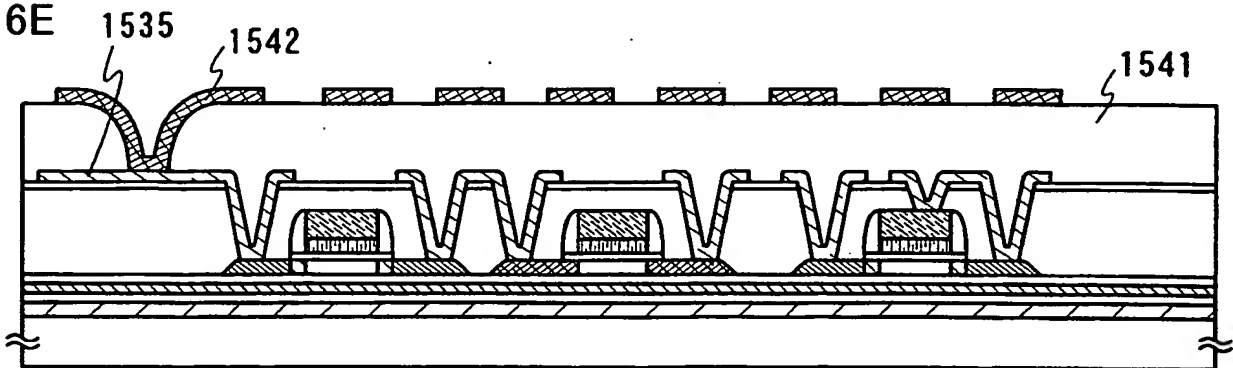


FIG. 17A

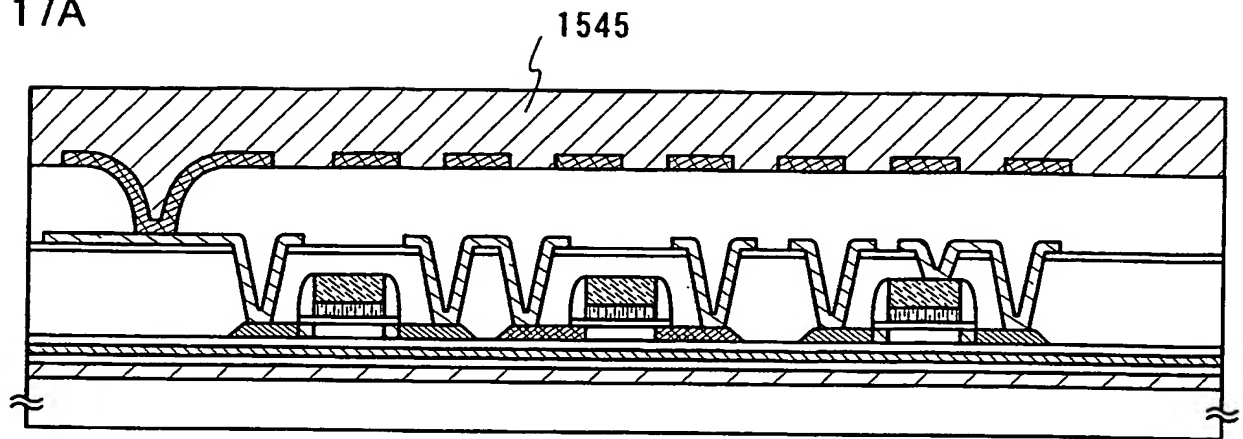


FIG. 17B

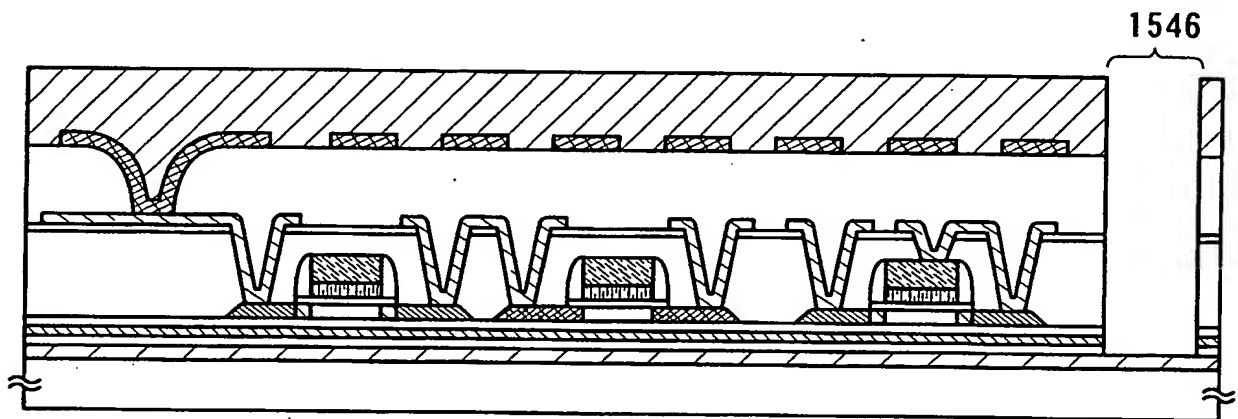


FIG. 17C

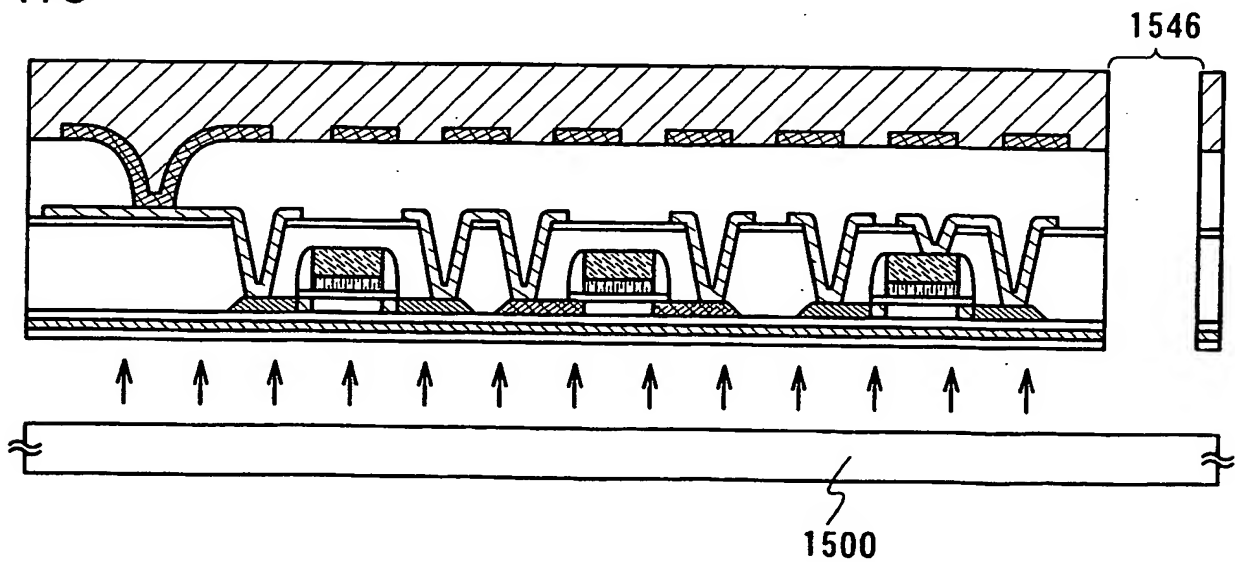


FIG. 18A

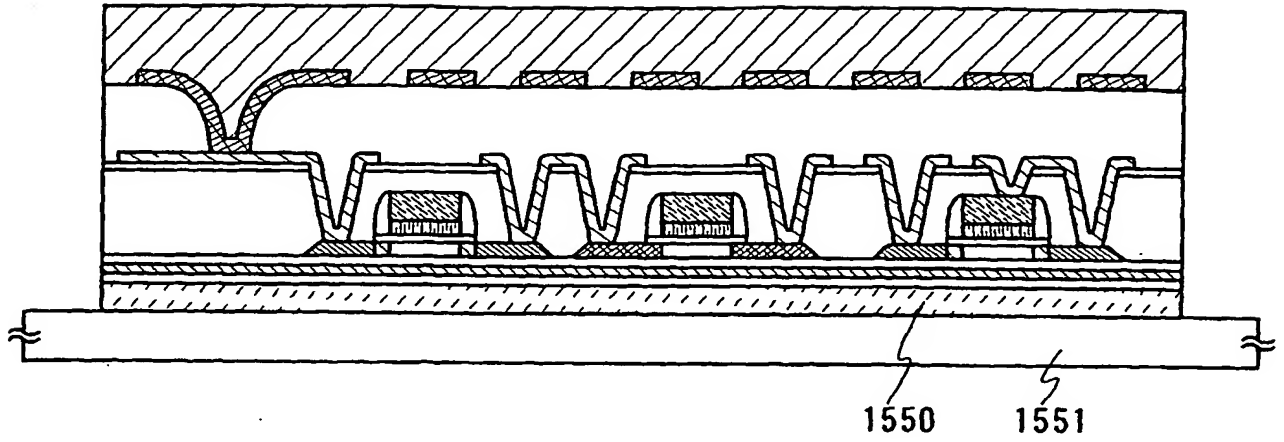


FIG. 18B

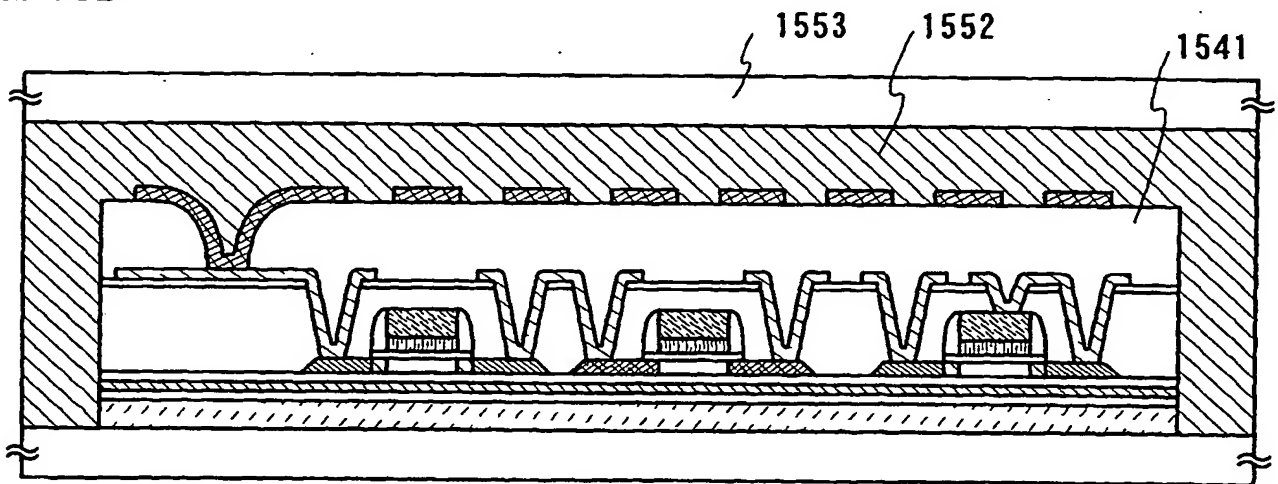


FIG. 19A

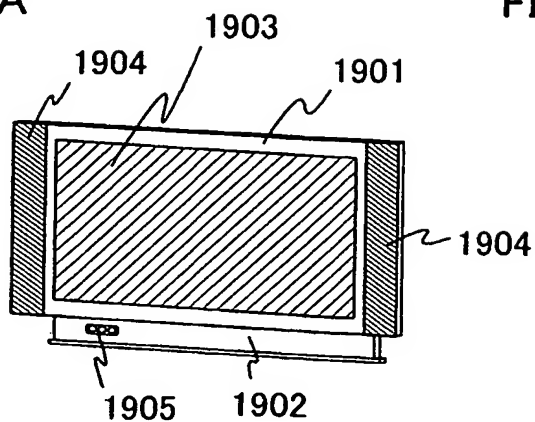


FIG. 19B

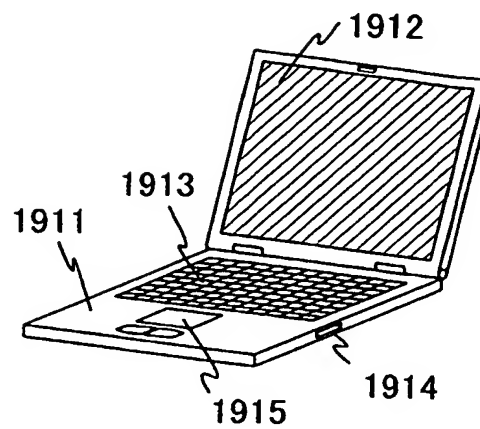


FIG. 19C

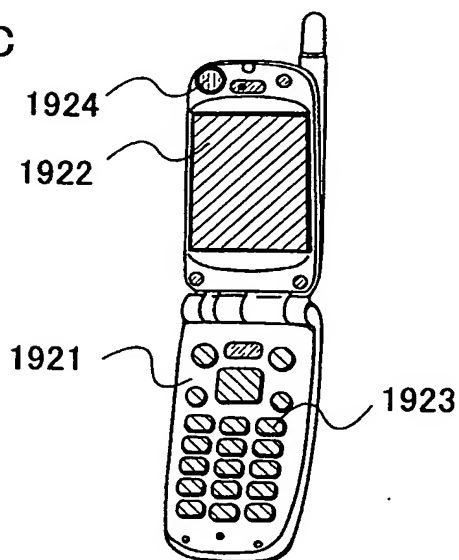


FIG. 19D

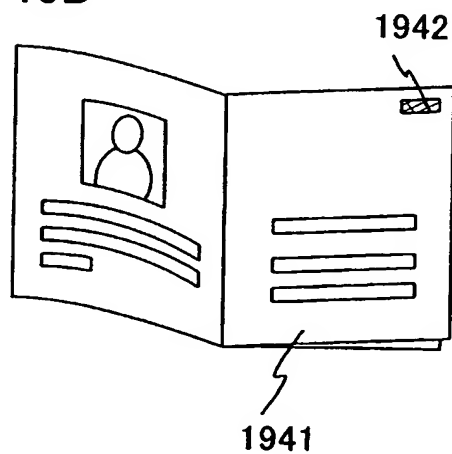
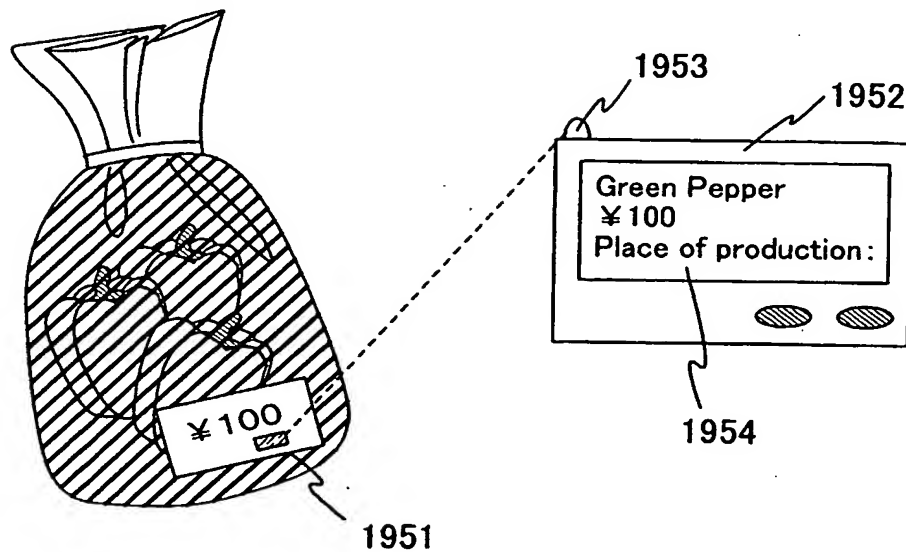


FIG. 19E



EXPLANATION OF REFERENCE

10: substrate, 11: base insulating film, 12: amorphous semiconductor film (semiconductor film having amorphous structure), 13: irradiation region, 14: crystalline semiconductor film (semiconductor film having crystalline structure), 15: arrow, 16: laser light, 17: semiconductor layer, 18: gate insulating film, 19: gate electrode, 20: source region, 21: drain region, 22: channel forming region, 23: interlayer insulating film, 24: source electrode, 25: drain electrode, 26: first LDD region, 27: second LDD region, 28: protective film, 29a: upper layer, 29b: lower layer, 30a: optical system, 30b: optical system, 31a: source region, 31b: drain region, 32: channel forming region, 33a: first interlayer insulating film, 33b: second interlayer insulating film, 36: first LDD region, 37: second LDD region, 38a: first gate insulating film, 38b: second gate insulating film, 39: gate electrode, 101: laser oscillator, 102: slit, 103: mirror, 104: first cylindrical lens, 105: second cylindrical lens, 106: semiconductor film, 107: substrate fixing stage, 108: X stage, 109: Y stage, 110: laser beam, 111: beam irradiation region, 610: substrate, 616: planarizing insulating film, 623: first electrode, 624: layer containing organic compound, 625: second electrode, 626: transparent protective layer, 627: transparent filler, 628: sealing agent, 629: insulator, 631: anisotropic conductive film, 632: FPC, 633: sealing substrate, 636: n-channel TFT, 637: p-channel TFT, 710: substrate having insulating surface, 711: base insulating film, 712: lower electrode, 713: first insulating film, 714: second insulating film, 715: channel forming region, 716: source region, 717: drain region, 718: second gate insulating film, 719a: first low-concentration impurity region, 719b: second low-concentration impurity region, 720a: upper layer of upper electrode, 720b: lower layer of upper electrode, 721: insulating film, 722: insulating film, 723: source wiring, 724: drain wiring, 1201: source-side driving circuit, 1202: pixel portion, 1203: gate-side driving circuit, 1204: sealing substrate, 1205: sealing agent, 1207: connecting region, 1208: terminal portion, 1209: FPC, 1210: substrate, 1301: driving IC, 1302: pixel portion, 1304: sealing substrate, 1305: sealing agent, 1307: connecting region, 1308: terminal portion, 1309: FPC, 1310: substrate, 1400: substrate, 1401: base insulating film, 1402: amorphous semiconductor film, 1405: laser light, 1406a: island-shaped semiconductor layer, 1406b: island-shaped semiconductor layer,

1406c: island-shaped semiconductor layer, 1406d: island-shaped semiconductor layer,
1406e: island-shaped semiconductor layer, 1408: gate insulating film, 1409a:
conductive film, 1409b: conductive film, 1410: resist mask, 1413: gate length, 1415:
resist mask, 1416a: impurity region, 1416b: impurity region, 1416c: impurity region,
5 1417: resist mask, 1418a: impurity region, 1418b: impurity region, 1419a: side wall,
1419b: sidewall, 1419c: sidewall, 1420a: high concentration impurity region, 1420b: high
concentration impurity region, 1420c: high concentration impurity region, 1421: resist
mask, 1422: first interlayer insulating film, 1423: second interlayer insulating film,
1425a: wiring, 1425b: wiring, 1425c: wiring, 1425d: wiring, 1425e: wiring, 1500: first
10 substrate, 1501: peeling layer, 1502: base insulating film, 1503: semiconductor film,
1504: semiconductor film having crystalline structure, 1506: island-shaped
semiconductor layer, 1507: island-shaped semiconductor layer, 1508: island-shaped
semiconductor layer, 1509: gate insulating film, 1510: gate electrode, 1511: gate
electrode, 1512: gate electrode, 1513: resist, 1515: resist, 1516: low-concentration
15 impurity region, 1517: low-concentration impurity region, 1518: resist, 1520:
high-concentration impurity region, 1521: insulating film, 1522: sidewall, 1523: sidewall,
1524: sidewall, 1526: resist, 1527: high concentration impurity region, 1528: high
concentration impurity region, 1530: n-channel TFT, 1531: p-channel TFT, 1532:
n-channel TFT, 1533: first interlayer insulating film, 1534: second interlayer insulating
20 film, 1535: wiring, 1536: wiring, 1537: wiring, 1538: wiring, 1539: wiring, 1541: third
interlayer insulating film, 1542: antenna, 1545: protective layer, 1546: groove, 1550:
adhesive agent, 1551: second substrate, 1552: adhesive agent, 1553: cover material,
1600: glass substrate, 1601: arithmetic logic unit, 1602: arithmetic logic unit
controller, 1603: instruction decoder, 1604: interrupt controller, 1605: timing controller,
25 1606: resistor, 1607: register controller, 1608: bus interface, 1609: ROM, 1620: ROM
interface, 1621: CLK 1, 1622: CLK 2, 1901: casing, 1902: support, 1903: display portion,
1904: speaker portion, 1905: video input terminal, 1911: casing, 1912: display portion,
1913: keyboard, 1914: external connection port, 1915: pointing mouse, 1921: casing,
1922: display portion, 1923: operation keys, 1924: sensor portion, 1941: passport, 1942:
30 radio frequency IC tag, 1951: radio frequency IC tag, 1952: reader, 1953: antenna

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portion, 1954: display portion